PTO-1449 REPRODUCED	ATTORNEY DOCKET NO. 2037.1004-007		APPLICATION NO. 10/645,330	
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION	FIRST NAMED INVENTOR Richard C. Foss		FILING DATE August 21, 2003	
August 18, 2004 (Use several sheets if necessary)	EXAMINER Michael T. Tran	CONFIRMATION NO. 7565		GROUP 2818

U.S. PATENT DOCUMENTS					
EXAM-INER INI-TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY		NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
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EXAMINER M. TRAN	DATE CONSIDERED 10/16/04

PTO-1449 REPRODUCED		ATTORNEY DOCKET NO. 2037.1004-007		APPLICATION NO. 10/645,330	
SUPPLEMENTAL INFORMATION DISCLOSURE CITATION IN AN APPLICATION August 18, 2004 (Use several sheets if necessary)		FIRST NAMED INVENTOR Richard C. Foss		FILING DATE August 21, 2003	
		EXAMINER Michael T. Tran		CONFIRMATION NO. 7565	GROUP 2818

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